

Magnetization reversal in Co/Cu/Co pillars by spin injection

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I Experiments on current-driven magnetization reversal

Test of models : field dependence

II Spin transfer in current-induced domain wall drag



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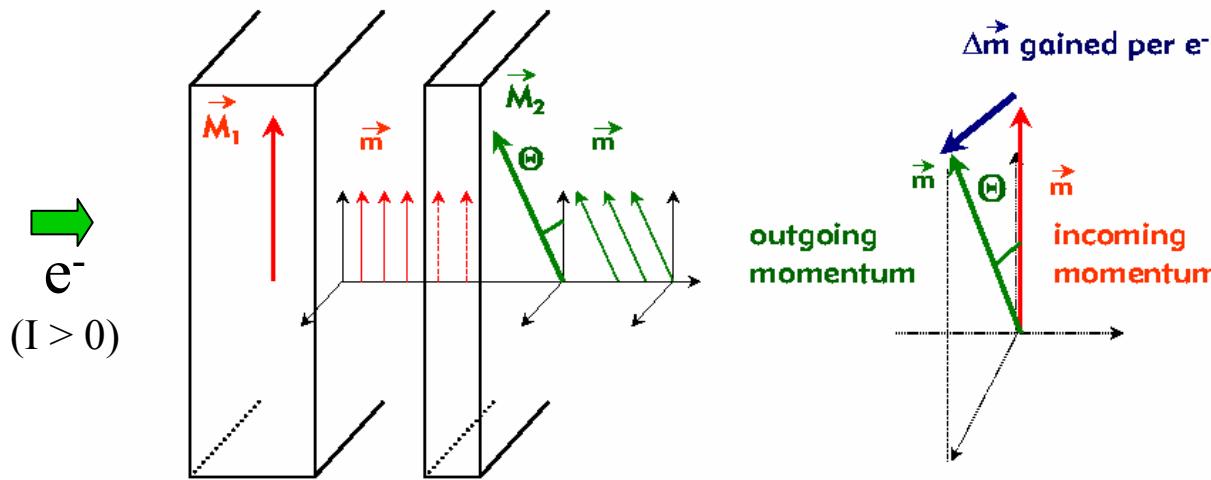
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Spin transfer models

J.C. Slonczewski, JMMM 159 (1996)



relaxation of **TRANSVERSE** polarization

$$\left(\frac{d\vec{m}}{dt} \right)_{\text{layer}}^{\text{injection}} = -P_I \frac{I}{e} \Delta \vec{m}_{\perp}$$

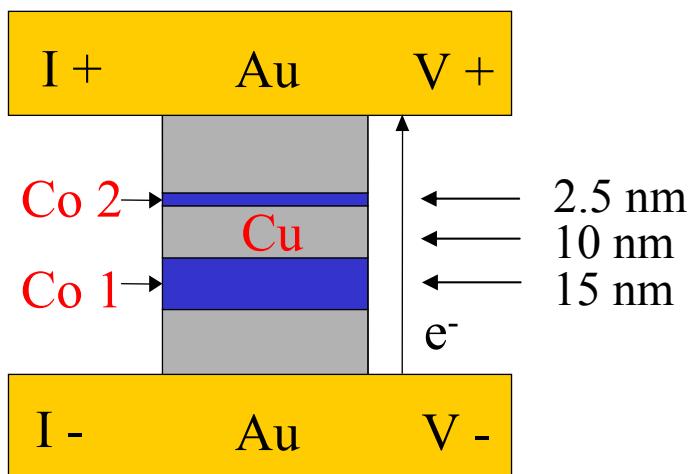
Conclusions : **current density $\approx 10^7 \text{ A.cm}^{-2}$**
torque : odd function of current



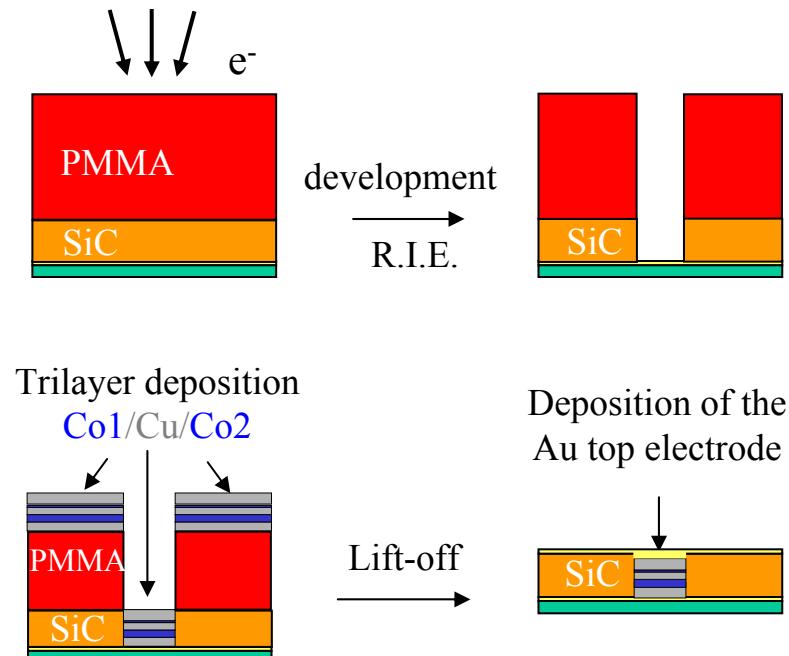
Sample fabrication

Trilayer Co/Cu/Co (dot size section : 200 x 600 nm²)

Co 2 Thin ferromagnetic layer : current sensitive



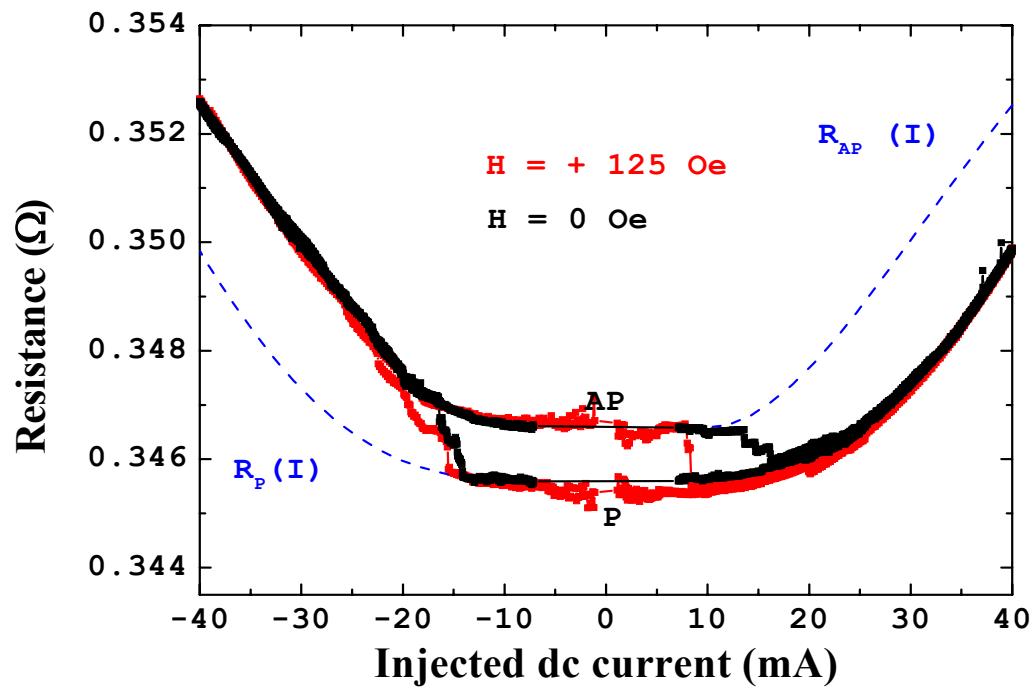
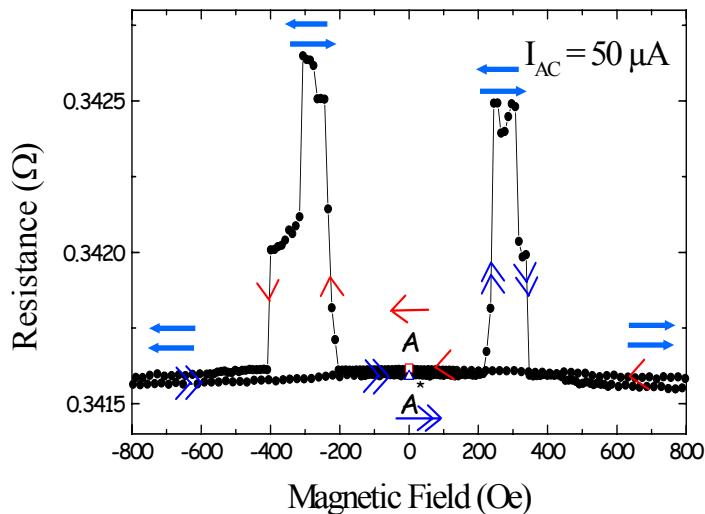
Co 1 Thick ferromagnetic layer : current polarizer



Measurements at high DC current with Happ < Han

T = 30 K

GMR = sensor



$$|J_c| \approx 10^7 \text{ A/cm}^2$$

A small magnetic field favors the P configuration

$\Rightarrow |J_c^{P \rightarrow AP}|$ increases and $|J_c^{AP \rightarrow P}|$ decreases



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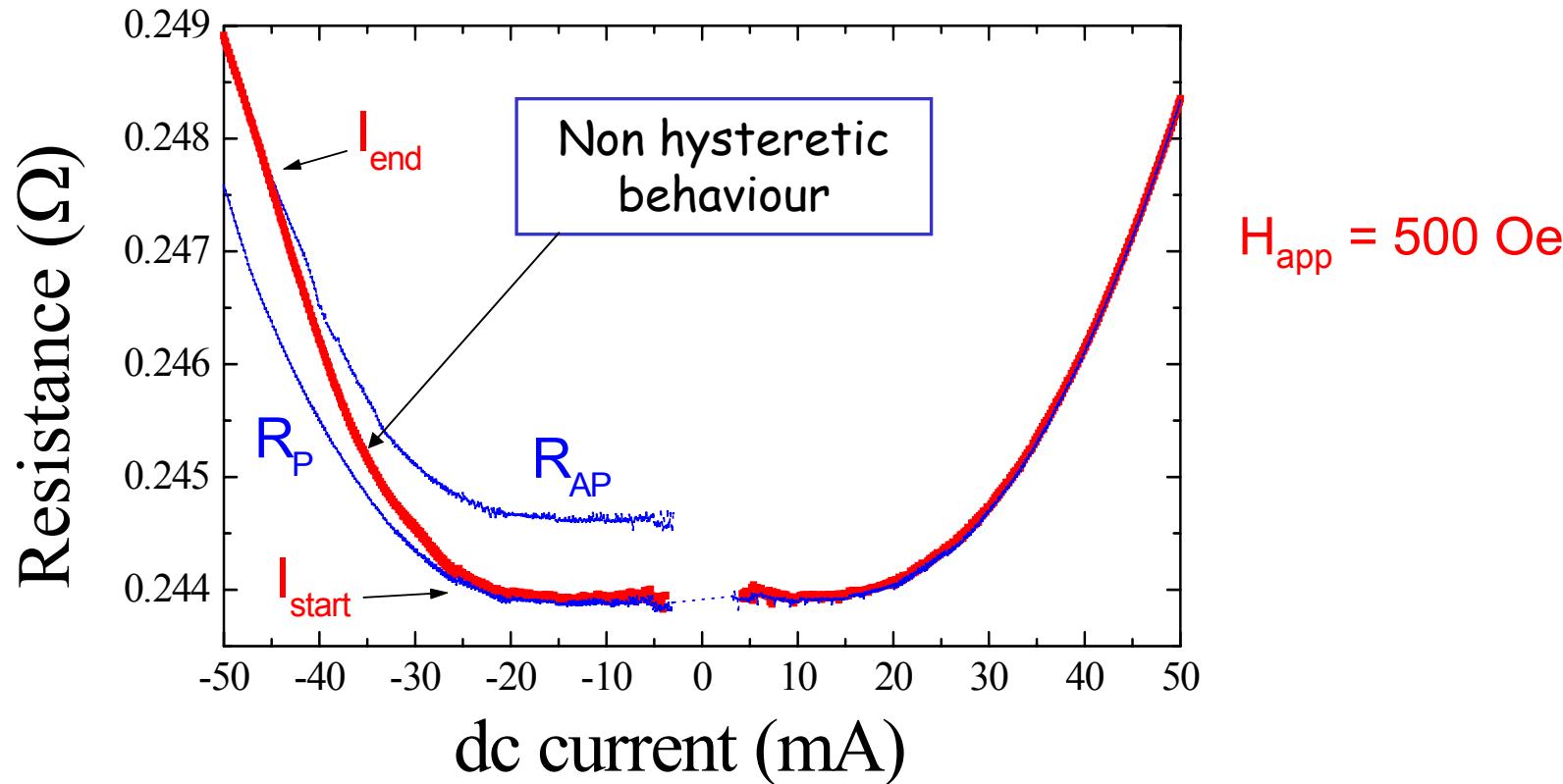
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Measurements at high DC current with Happ > Han

T = 30 K

Co (150A)/Cu(100A)/Co(25A)

dot size : 200 x 600 nm²



Calculation of the torque : LLG equation

$$\frac{d\vec{m}}{dt} = -\gamma_0 \vec{m} \times [H_{eff}\vec{u}_x - H_d(\vec{m} \cdot \vec{u}_z)\vec{u}_z] + \alpha \vec{m} \times \frac{d\vec{m}}{dt} - \mathfrak{J} \vec{m} \times (\vec{m} \times \vec{u}_x)$$

$$\mathfrak{J} = P_m \frac{g\mu_B}{etM_s} j$$

General case : coupled equations

\mathbf{m} close to P and AP : uncoupled $\longrightarrow m_y, m_z = A e^{x_1 t} + B e^{x_2 t}$

Ex : for a P to AP reversal

- ① Instability of P state
- ② Stability of AP state



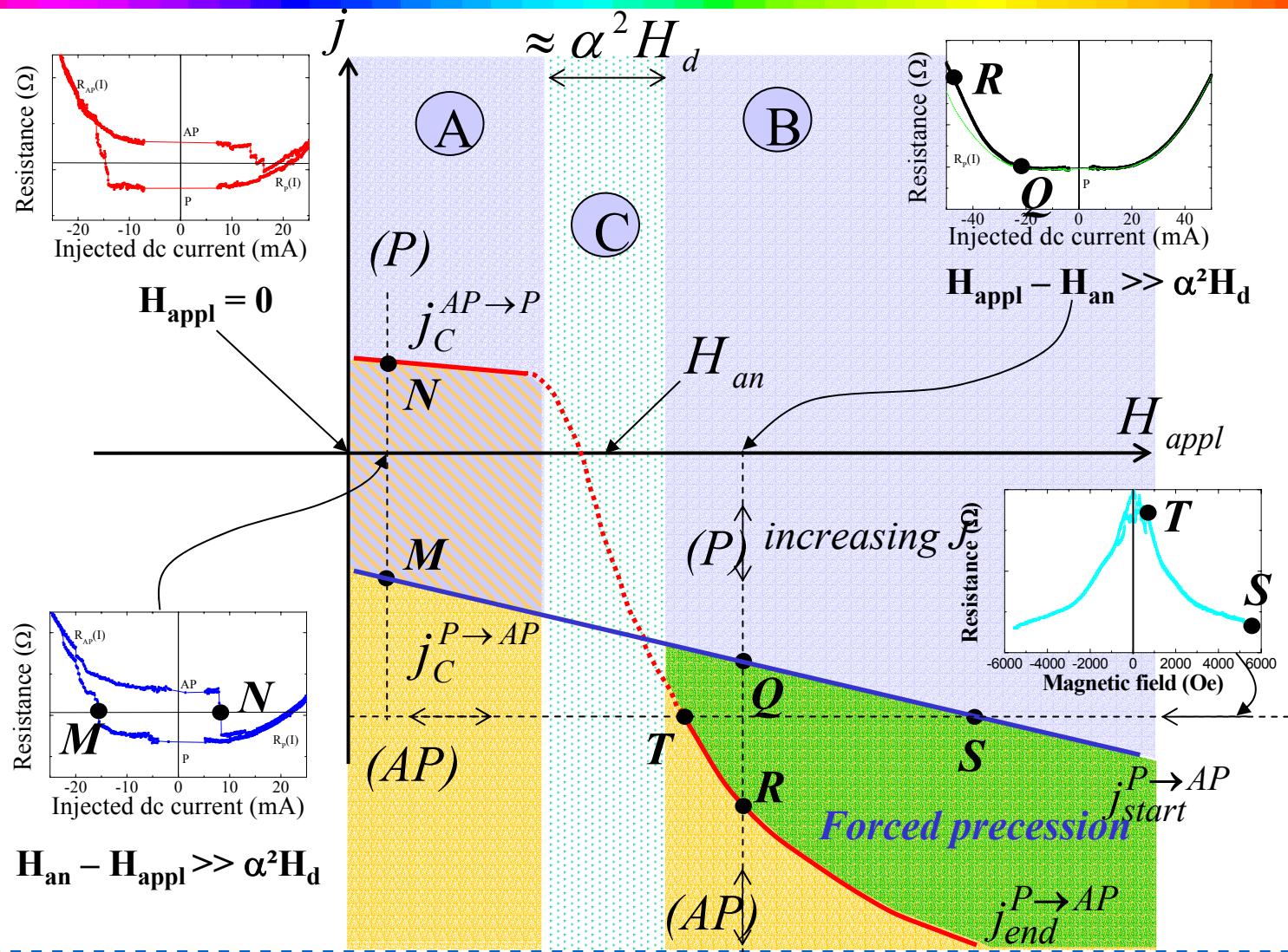
sign of the real part of
 x_1 and x_2

holds for precessional and non precessional modes

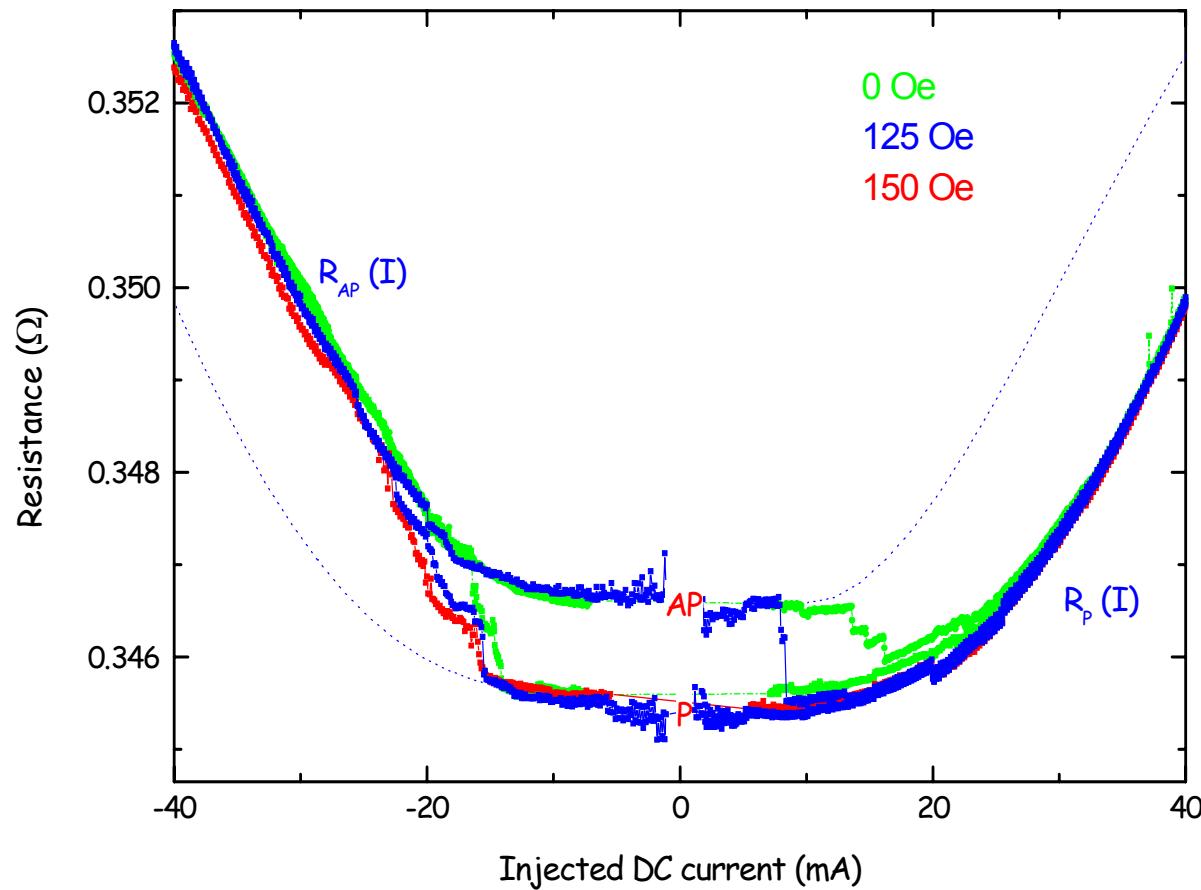
(Katine *et al* : discussion of stability limited to the field range of periodic precession)



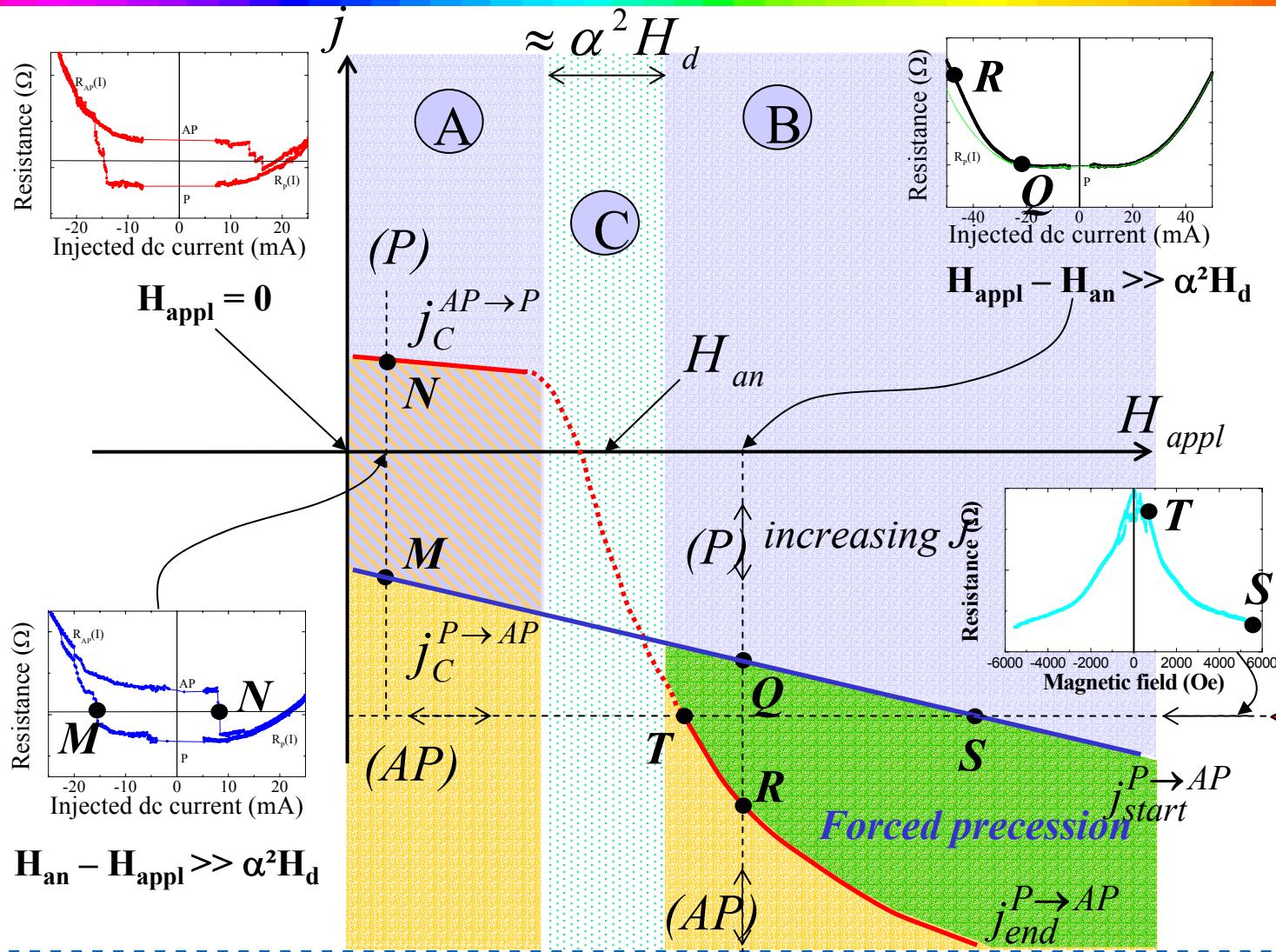
Summary



Transition between the two regimes : Happ \approx Han



R(H) at fixed high I_{inj}

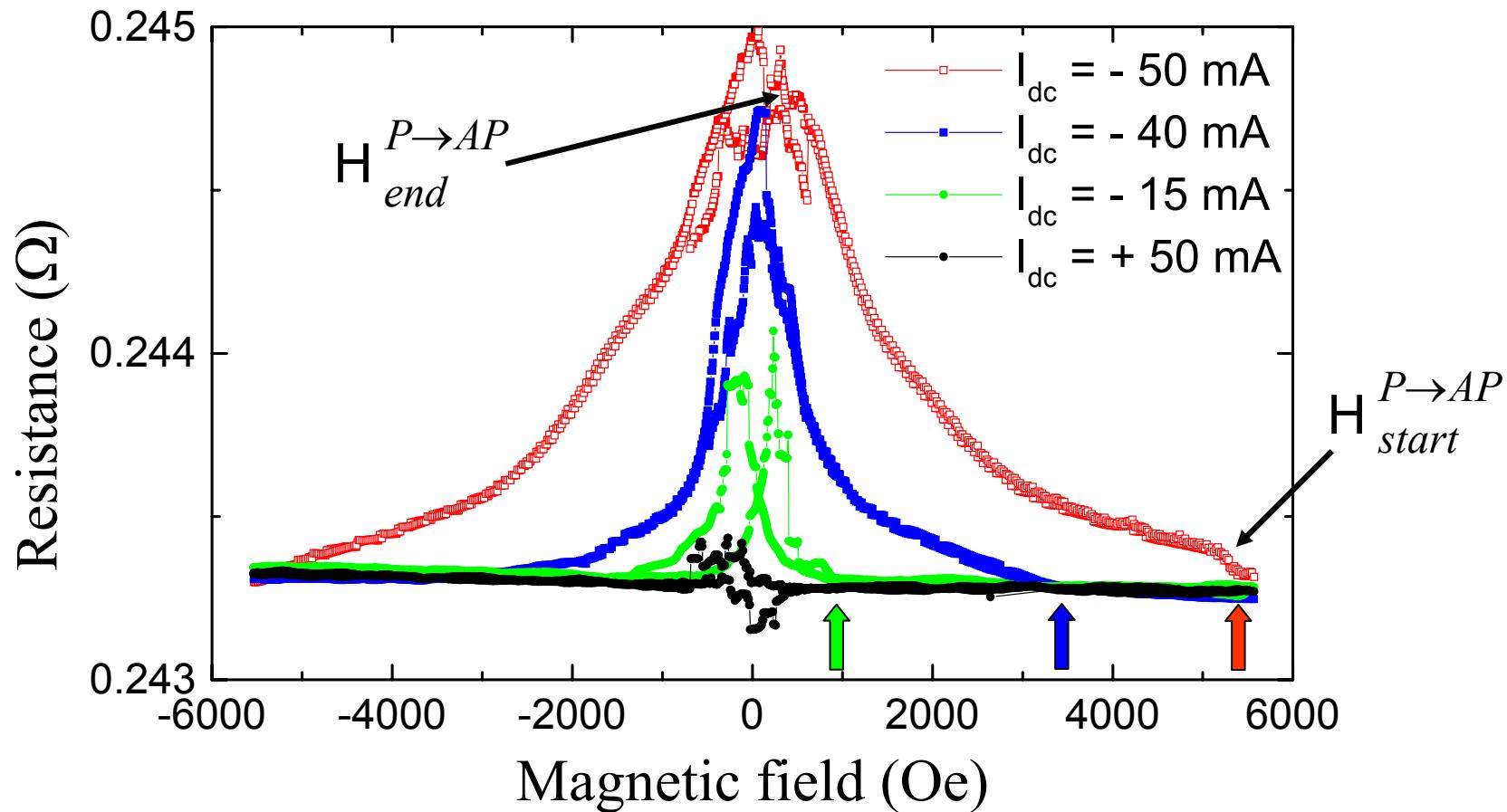


Measurements at high DC current : R(H)

T = 30 K

Co (150A)/Cu(100A)/Co(25A)

dot size : 200 x 600 nm²

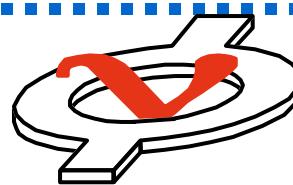


J. Grollier et al., Appl. Phys. Lett. 78, 3663 (2001)



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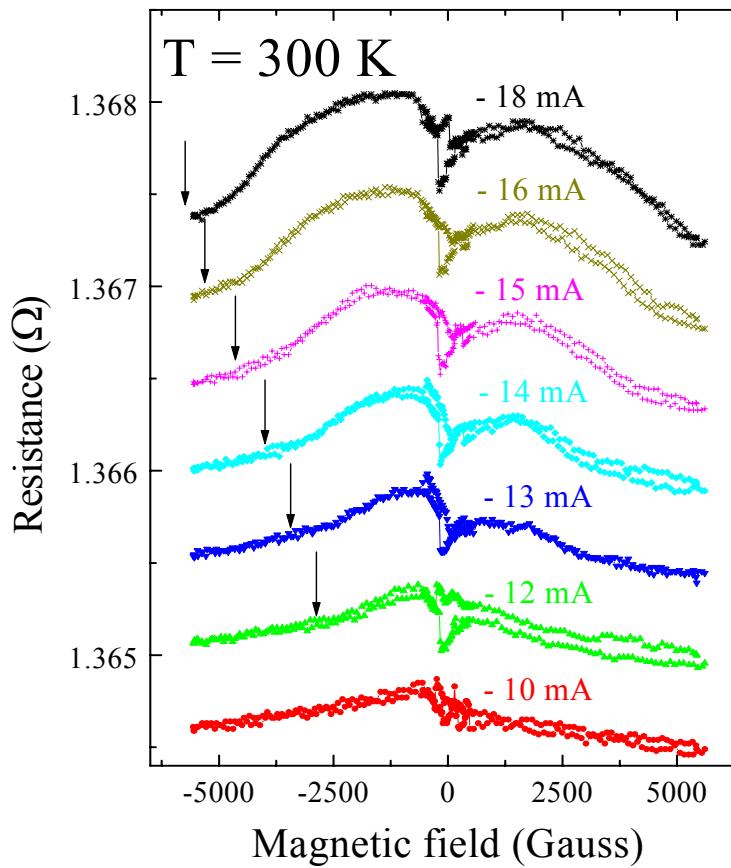
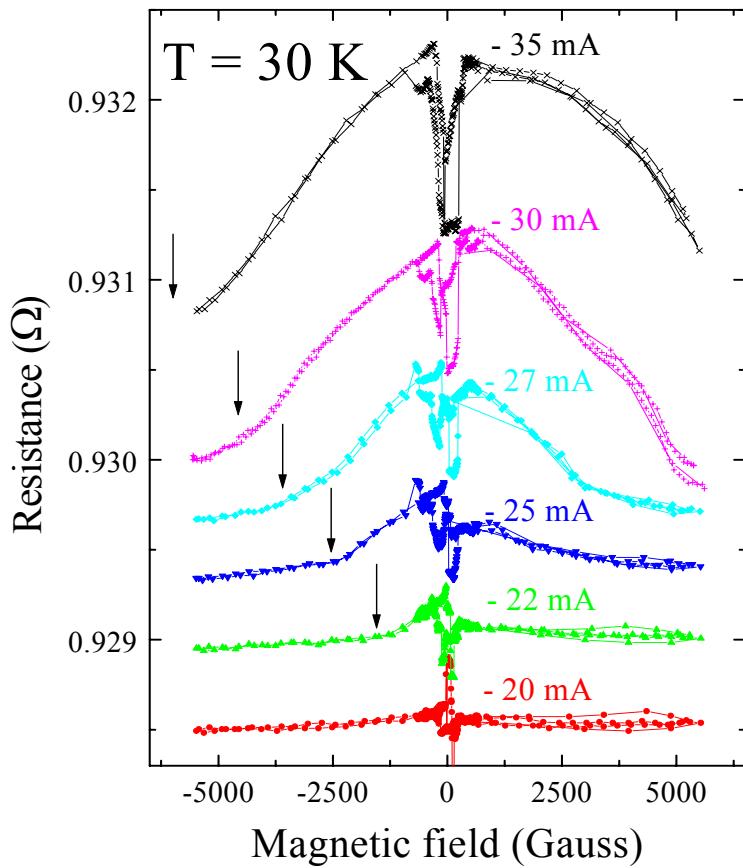


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Field dependence of the critical current : exp.

Example for other samples :

200 x 400 nm² Co(300A)/Cu(100A)/Co(50A) pillar



Field dependence of the critical current density

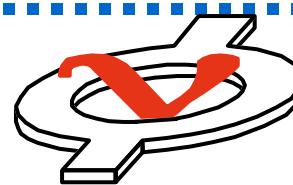
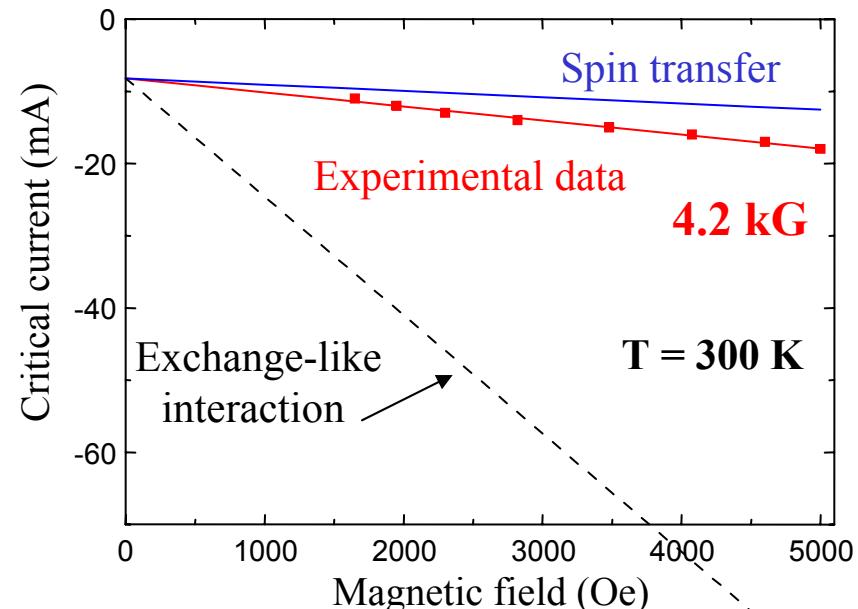
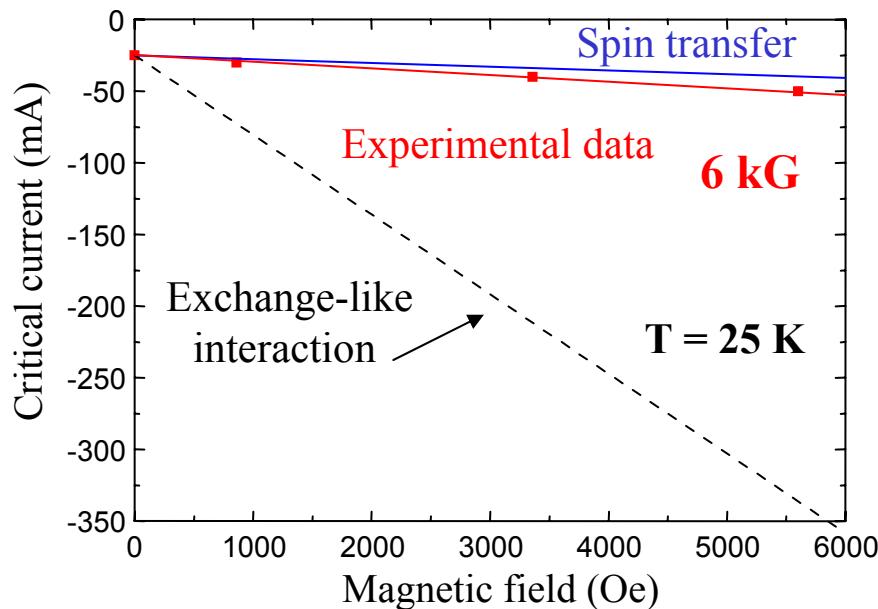
- Spin transfer model (cf. Slonczewski)
- Interaction picture (cf. Heide)

$$j_C^P = j_C(H=0)^P \times \left[1 + \frac{H_{app}}{H_{an} + H_d / 2} \right]$$

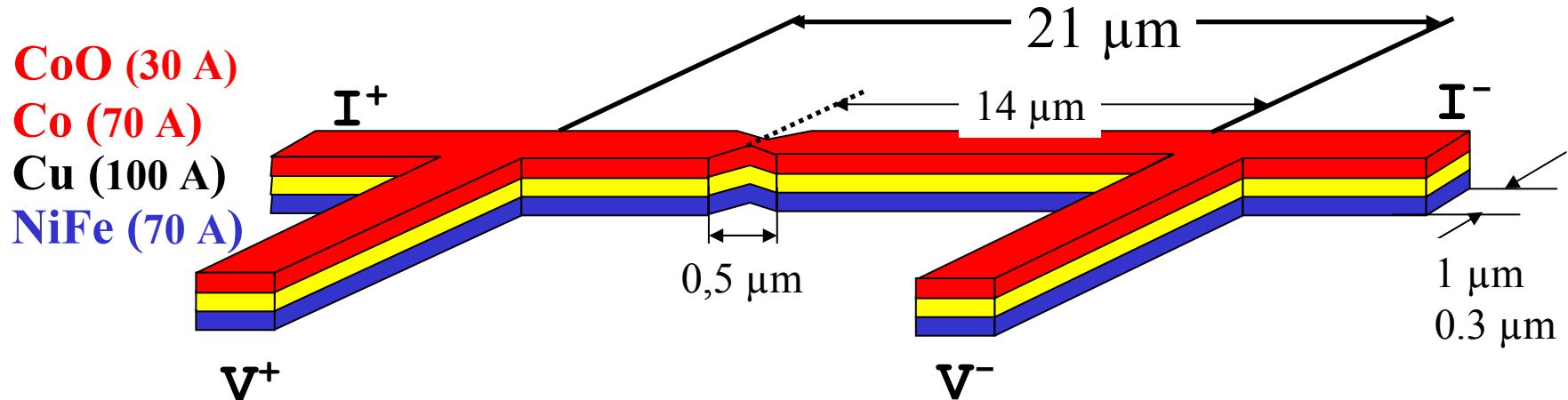
8.5 kG

$$j_C^P = j_C(H=0)^P \times \left[1 + \frac{H_{app}}{H_C} \right]$$

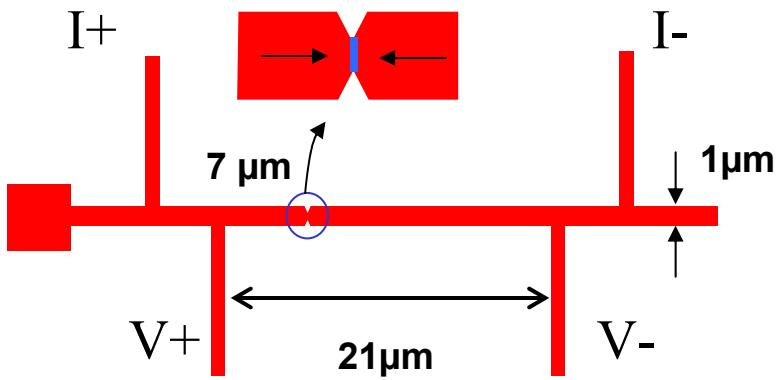
0.4 kG



Switching a spin valve by current-induced DW drag



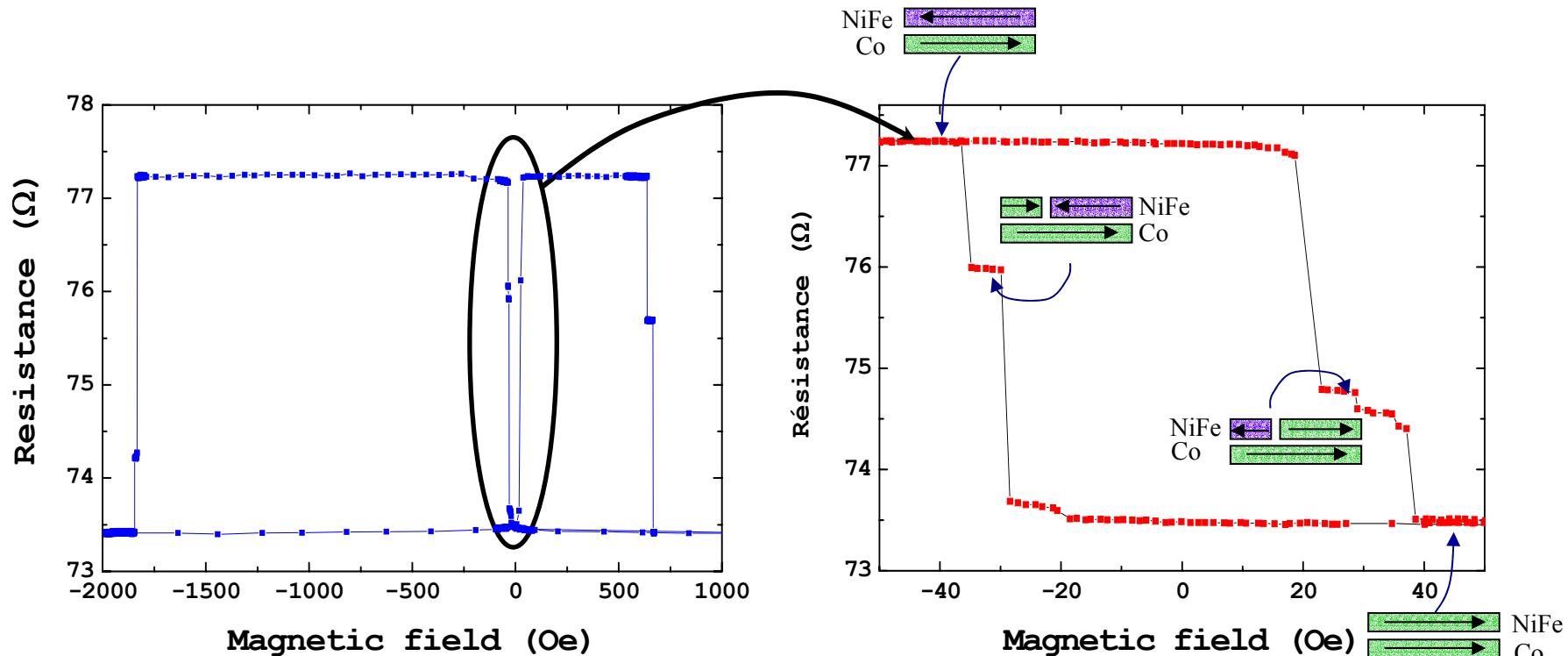
Top view :



S.E.M. image :



GMR at low temperature



$I = 5 \mu\text{A}$ and $T = 3 \text{ K}$



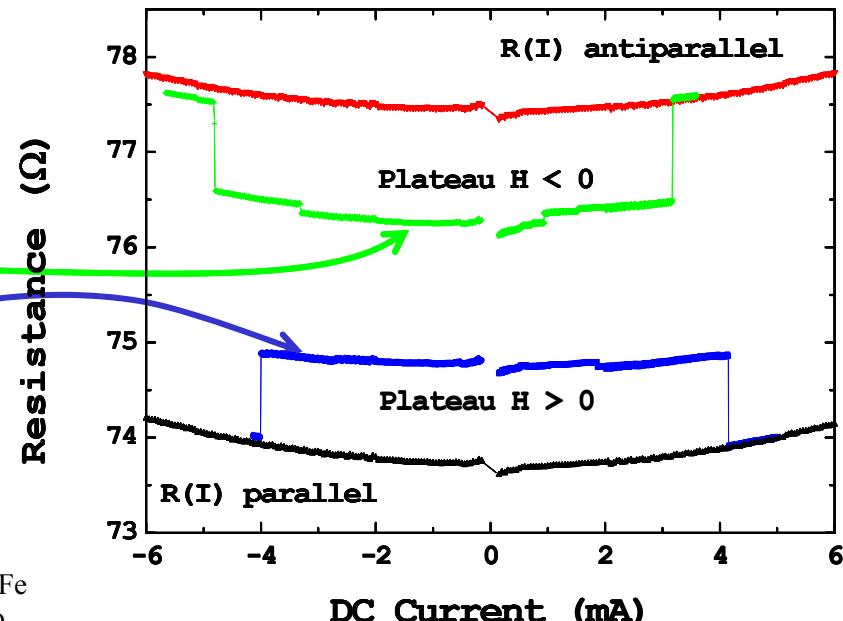
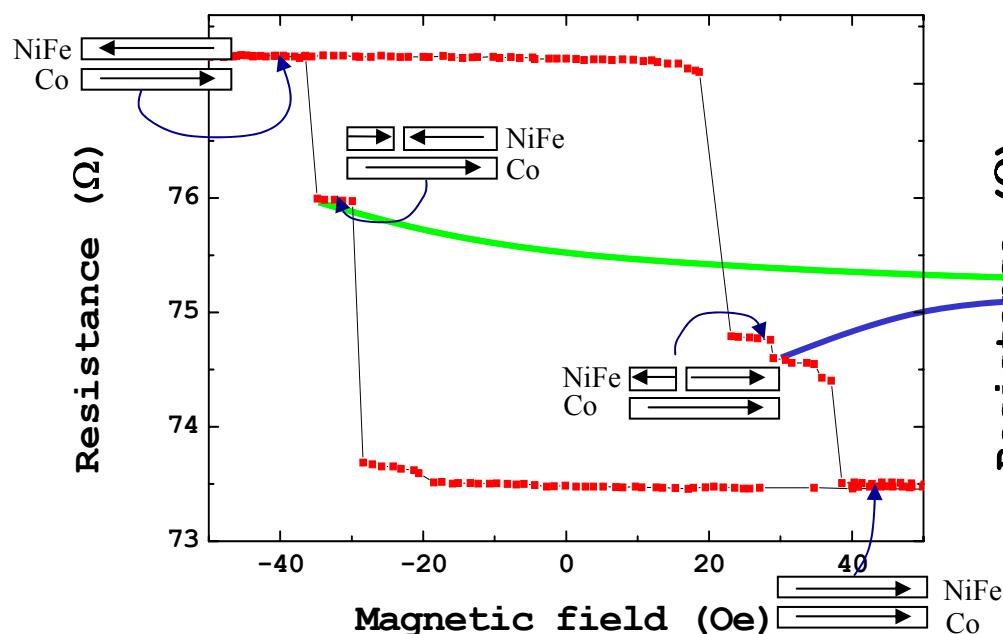
$\text{GMR} \approx 5 \%$

Stripe width = $1 \mu\text{m}$



Domain wall motion induced by a high dc current

Stripe width = 1 μm



➤ motion in the same direction whatever the current direction

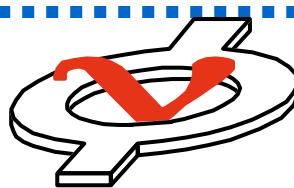
$$\text{Critical current density} \approx 2.6 \cdot 10^7 \text{ A/cm}^2$$

J. Grollier et al., Appl. Phys. Lett. 92, 4825 (2002)



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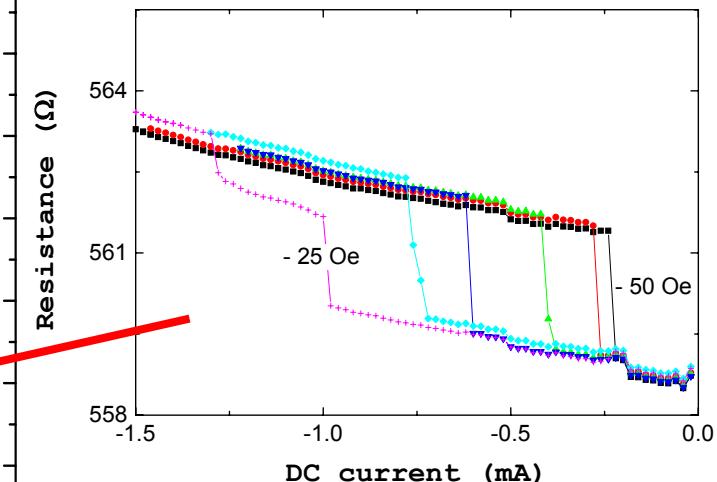
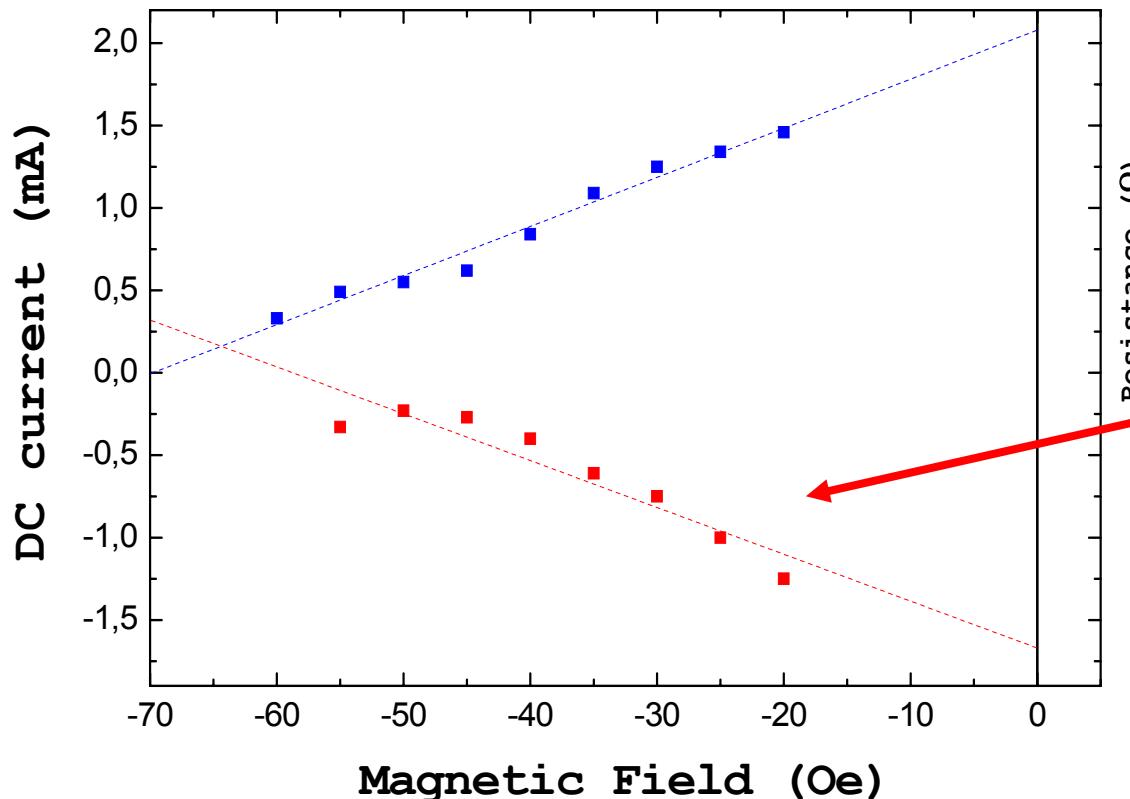
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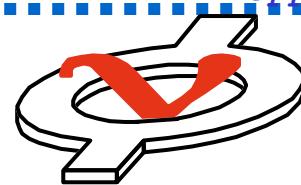
Field dependence of the critical current

Stripe width = 0,3 μm



Critical current density :
 $\approx 2 \cdot 10^7 \text{ A/cm}^2$ for $H_{\text{appl}} = -60 \text{ Oe}$

$\approx 2 \cdot 10^8 \text{ A/cm}^2$ for $H_{\text{appl}} = 0 \text{ Oe}$



Origins of the effect ?

3) Spin tranfer

pros : critical current densities in agreement with spin transfer models

cons : the effect is independent of the current sign

2) Oersted field

pros : locally, $H_{\text{longitudinal}}$ reaches about 30 Oe

cons : the longitudinal component is in average zero in the sample

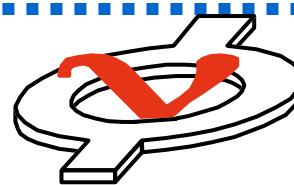
1) Heating ?

DW distortion and destabilization by one of these mechanisms ?



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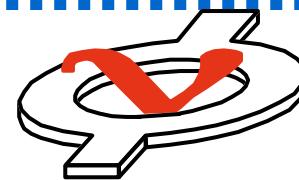
Conclusions and perspectives

- Reversal of magnetization by spin injection in pillar-shaped Co/Cu/Co tri-layers
- Spin transfer vs. interaction model (field dependence)
- Spin transfer : qualitative agreement with experiments
- Decrease the critical currents : interface resistances, spin diffusion length, sample section ...
- Study of spin transfer effect on other structures: case of the DW motion induced by a DC current
- Dynamics ?
- Promising applications (commutation of spin electronic devices)



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